



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



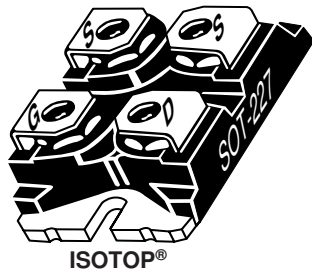
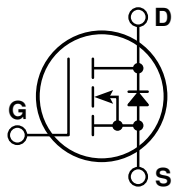
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APT40M75JN 400V 56.0A 0.075Ω
 APT40M90JN 400V 51.0A 0.090Ω

"UL Recognized" File No. E145592 (S)

POWER MOS IV®

SINGLE DIE ISOTOP® PACKAGE

N-CHANNEL ENHANCEMENT MODE HIGH VOLTAGE POWER MOSFETS

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT 40M75JN	APT 40M90JN	UNIT
V_{DSS}	Drain-Source Voltage	400	400	Volts
I_D	Continuous Drain Current @ $T_C = 25^\circ\text{C}$	56	51	Amps
I_{DM}, I_{LM}	Pulsed Drain Current ^① and Inductive Current Clamped	224	204	
V_{GS}	Gate-Source Voltage	±30		Volts
P_D	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	520		Watts
	Linear Derating Factor	4.16		W/°C
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150		°C
T_L	Lead Temperature: 0.063" from Case for 10 Sec.	300		

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions / Part Number	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage ($V_{GS} = 0V, I_D = 250 \mu\text{A}$)	APT40M75JN	400		Volts
		APT40M90JN	400		
$I_{D(ON)}$	On State Drain Current ^② ($V_{DS} > I_{D(ON)} \times R_{DS(ON)}$ Max, $V_{GS} = 10V$)	APT40M75JN	56		Amps
		APT40M90JN	51		
$R_{DS(ON)}$	Drain-Source On-State Resistance ^② ($V_{GS} = 10V, 0.5 I_D$ [Cont.])	APT40M75JN		0.075	Ohms
		APT40M90JN		0.090	
I_{DSS}	Zero Gate Voltage Drain Current ($V_{DS} = V_{DSS}, V_{GS} = 0V$)			250	μA
	Zero Gate Voltage Drain Current ($V_{DS} = 0.8 V_{DSS}, V_{GS} = 0V, T_C = 125^\circ\text{C}$)			1000	
I_{GSS}	Gate-Source Leakage Current ($V_{GS} = \pm 30V, V_{DS} = 0V$)			±100	nA
$V_{GS(TH)}$	Gate Threshold Voltage ($V_{DS} = V_{GS}, I_D = 2.5\text{mA}$)	2		4	Volts

THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.24	°C/W
$R_{\theta CS}$	Case to Sink (Use High Efficiency Thermal Joint Compound and Planer Heat Sink Surface.)		0.06		

CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

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DYNAMIC CHARACTERISTICS

APT40M75/40M90JN

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1\text{ MHz}$		5630	6800	pF
C_{oss}	Output Capacitance			1320	1950	
C_{rss}	Reverse Transfer Capacitance			510	720	
Q_g	Total Gate Charge ③	$V_{GS} = 10V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_D [\text{Cont.}] @ 25^\circ\text{C}$		241	370	nC
Q_{gs}	Gate-Source Charge			34	50	
Q_{gd}	Gate-Drain ("Miller") Charge			117	180	
$t_d(\text{on})$	Turn-on Delay Time	$V_{GS} = 15V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_D [\text{Cont.}] @ 25^\circ\text{C}$ $R_G = 0.6\Omega$		16	32	ns
t_r	Rise Time			31	62	
$t_d(\text{off})$	Turn-off Delay Time			45	70	
t_f	Fall Time			13	26	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
I_S	Continuous Source Current (Body Diode)	APT40M75JN		56	Amps
		APT40M90JN		51	
I_{SM}	Pulsed Source Current ① (Body Diode)	APT40M75JN		224	Amps
		APT40M90JN		204	
V_{SD}	Diode Forward Voltage ② ($V_{GS} = 0V, I_S = -I_D [\text{Cont.}]$)			1.8	Volts
t_{rr}	Reverse Recovery Time ($I_S = -I_D [\text{Cont.}], di_S/dt = 100A/\mu s$)		370	740	ns
Q_{rr}	Reverse Recovery Charge ($I_S = -I_D [\text{Cont.}], di_S/dt = 100A/\mu s$)		8	16	μC

PACKAGE CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
L_D	Internal Drain Inductance (Measured From Drain Terminal to Center of Die.)		3		nH
L_S	Internal Source Inductance (Measured From Source Terminals to Source Bond Pads)		5		
$V_{isolation}$	RMS Voltage (50-60 Hz Sinusoidal Waveform From Terminals to Mounting Base for 1 Min.)	2500			Volts
$C_{isolation}$	Drain-to-Mounting Base Capacitance ($f = 1\text{MHz}$)		35		pF
Torque	Maximum Torque for Device Mounting Screws and Electrical Terminations.			13	in-lbs

① Repetitive Rating: Pulse width limited by maximum junction temperature. See Transient Thermal Impedance Curve. (Fig.1)

② Pulse Test: Pulse width < 380 μs , Duty Cycle < 2%

③ See MIL-STD-750 Method 3471

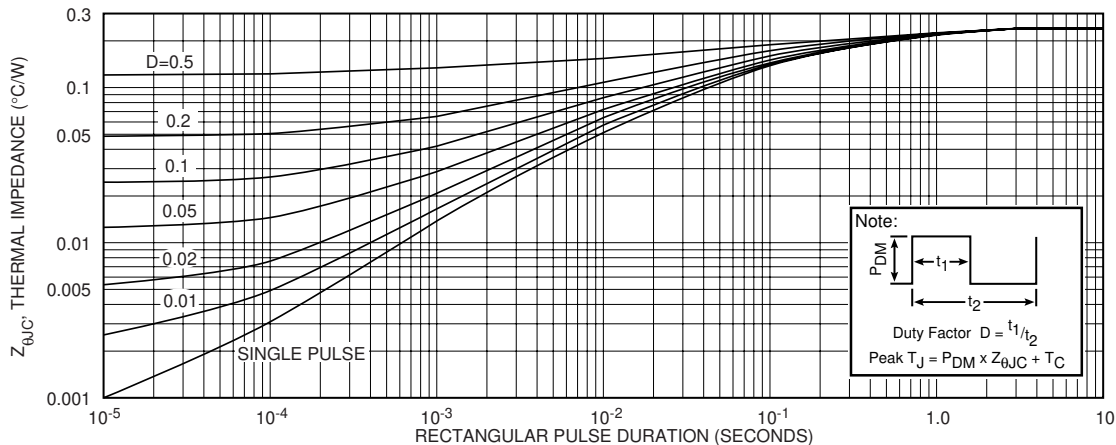


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

APT40M75/40M90JN

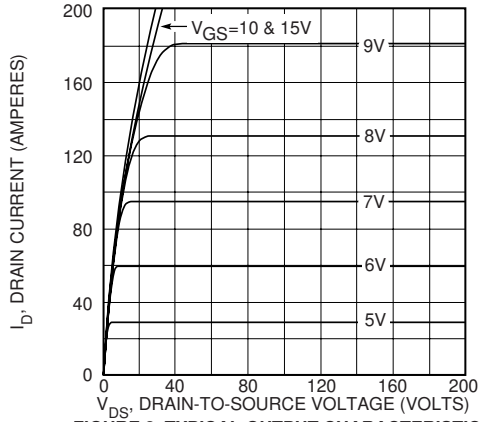


FIGURE 2, TYPICAL OUTPUT CHARACTERISTICS

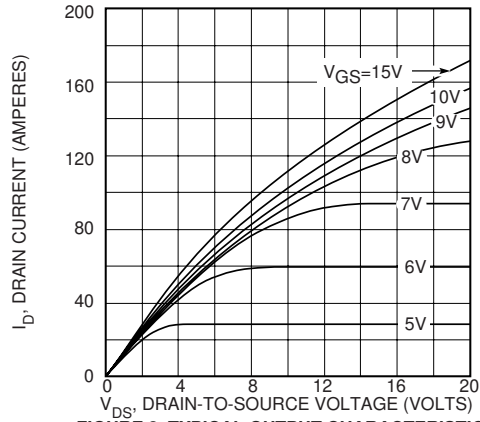


FIGURE 3, TYPICAL OUTPUT CHARACTERISTICS

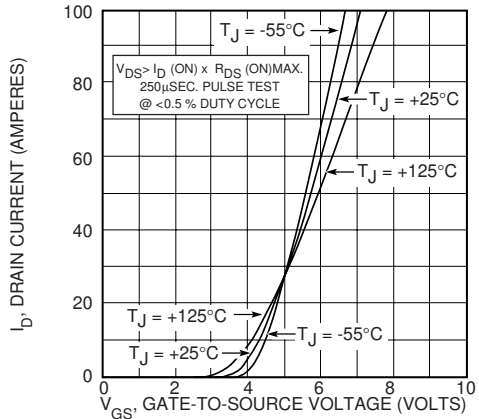


FIGURE 4, TYPICAL TRANSFER CHARACTERISTICS

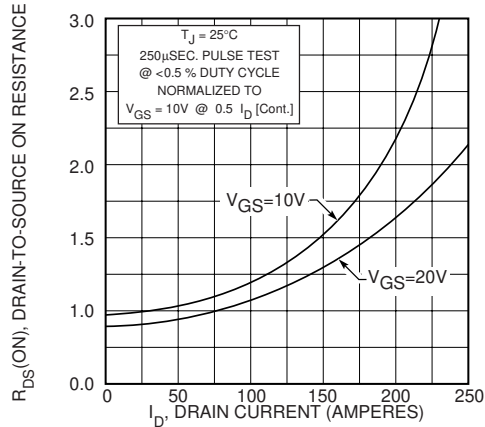


FIGURE 5, $R_{DS(ON)}$ vs DRAIN CURRENT

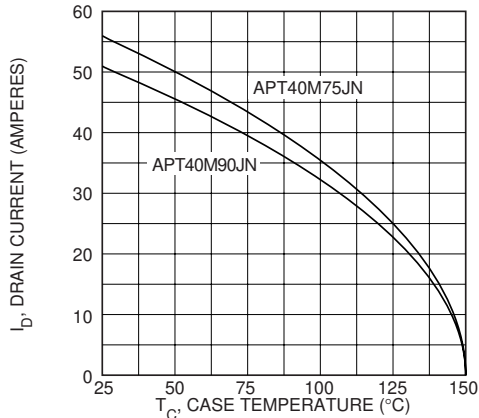


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

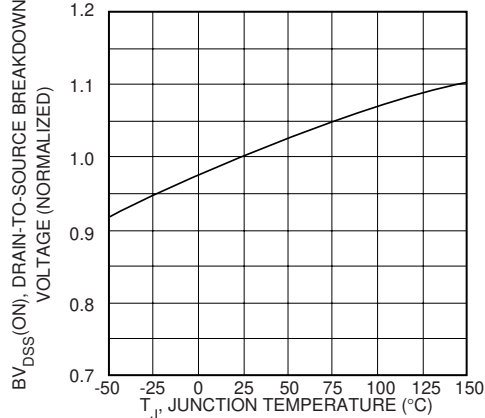


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

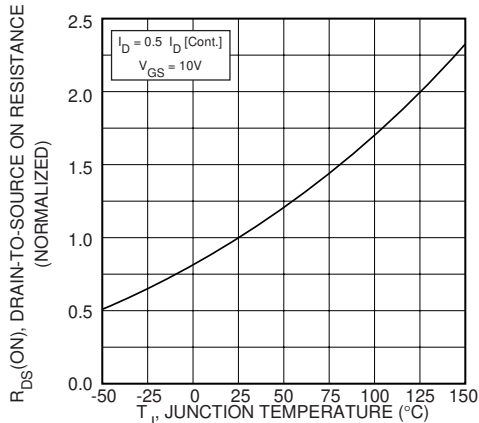


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

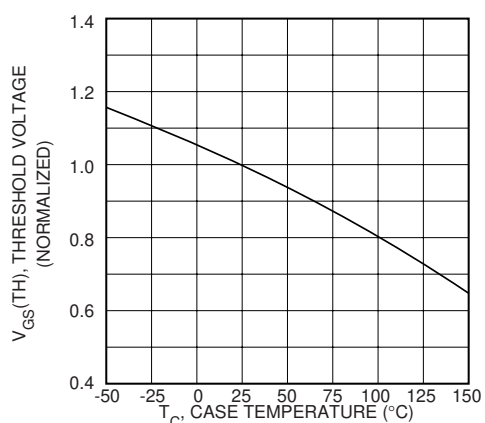


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

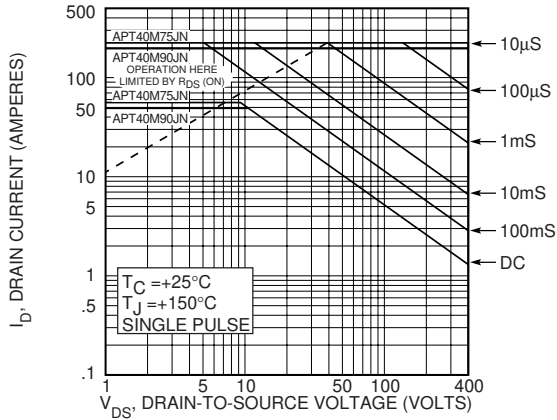


FIGURE 10, MAXIMUM SAFE OPERATING AREA

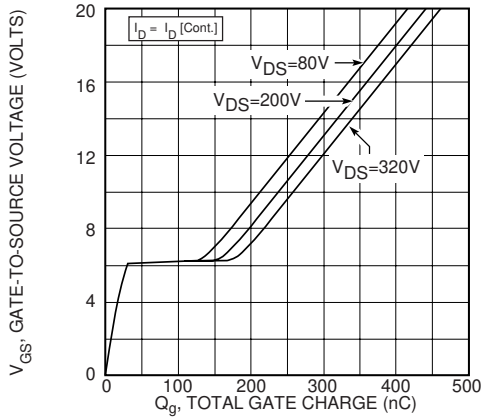


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

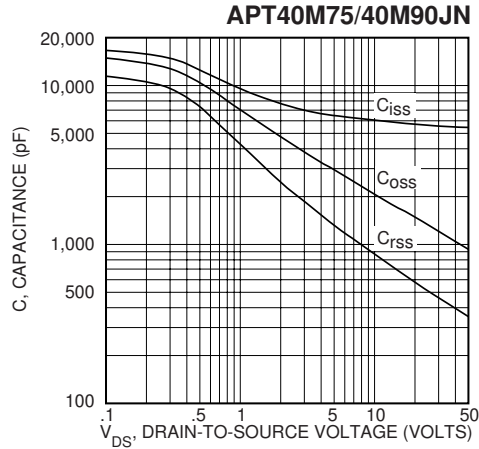


FIGURE 11, TYPICAL CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

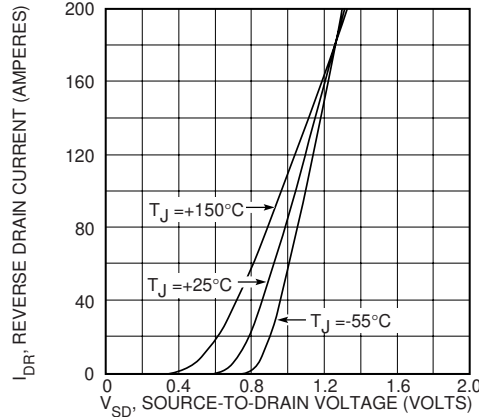
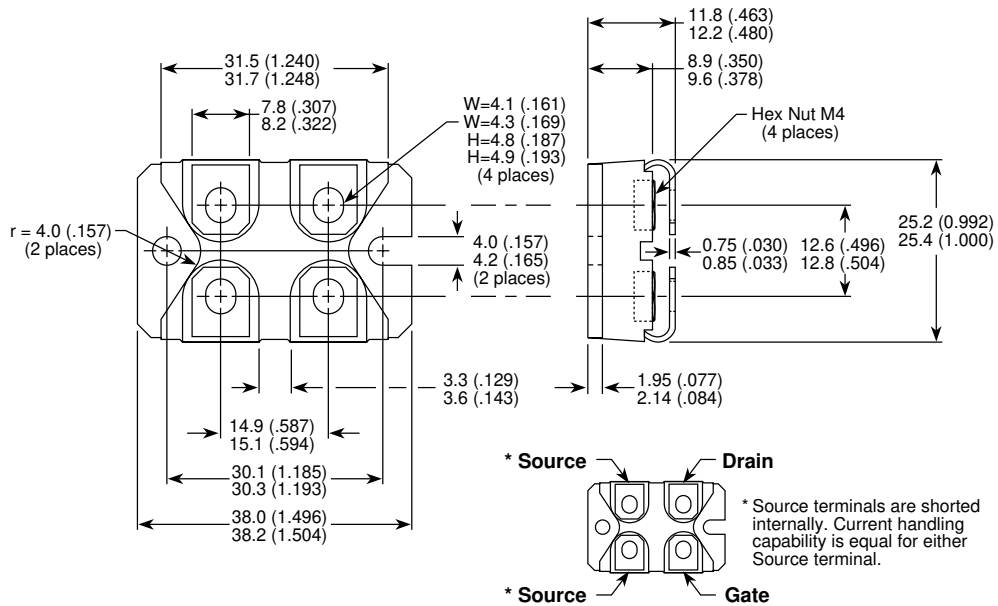


FIGURE 13, TYPICAL SOURCE-DRAIN DIODE FORWARD VOLTAGE

APT Reserves the right to change, without notice, the specifications and information contained herein.

SOT-227 (ISOTOP®) Package Outline



Dimensions in Millimeters and (Inches)

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